

**SILICON PRIME WAFERS - SPECIFICATION 100/P/SS/15-25**

Rev. 2.1 / 12.04.02

**1. Material Parameters**

1.1 Growth method	Czochralski
1.2 Conductivity type	P
1.3 Dopant	Boron
1.4 Orientation	<100>
1.5 Off-orientation	0° ± 0.5°
1.6 Resistivity range	15 - 25 ohm-cm
1.7 Dislocation density	< 100 / cm <sup>2</sup>

**2. Dimensional Parameters**

2.1 Diameter	100 ± 0.2 mm
2.2 Thickness	525 ± 20 µm
2.3 Primary flat orientation	<110> ± 1°
2.4 Primary flat length	32.5 ± 2.5 mm
2.5 Secondary flat location	90° CW from primary flat
2.6 Secondary flat length	18 ± 2 mm
2.7 Total thickness variation, max	10 µm
2.8 Bow, max	20 µm
2.9 Warp, max	20 µm
2.10 Edge contour	As per SEMI MI-0996
2.11 Wafer ID marking	As specified

**3. Front Surface Parameters**

3.1 Particules, max	0.075 / cm <sup>2</sup>
3.2 Scratches	None
3.3 Haze	None
3.4 Edge chips and indents	None
3.5 Orange peel	None
3.6 Saw marks	None
3.7 Other surface defects	None

**4. Back Surface Parameters**

4.1 Back surface	Etched
4.2 Edge chips	None
4.3 Saw marks	None